Abstracts

Broad-Band GaAs FET Amplifier Design Using Negative-Image Device Models

M.W. Medley, Jr. and J.L. Allen. "Broad-Band GaAs FET Amplifier Design Using Negative-Image Device Models." 1979 Transactions on Microwave Theory and Techniques 27.9 (Sep. 1979 [T-MTT]): 784-788.

A new technique is presented for determining equivalent source and load device models applicable to GaAs FET or other devices for which measured data is available. The new technique provides a more accurate starting point for matching network synthesis, better prediction of achievable circuit performance, and does not require the unilateral device assumption. Simple computer optimization and elements with negative reactance slope parameters are utilized. A description of the method and examples of its application to GaAs FET amplifier design are presented.

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